

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method for use in designing a reticle for exposing a substrate during production of a circuit, comprising:

determining the relative isolation of first type features to be produced using the reticle with respect to adjacent features;

sizing first type apertures in the reticle corresponding to the first type features using different sizing rules depending on the relative isolation of the first type features;

determining dimensions of second type features to be produced using the same reticle; and

sizing second type apertures corresponding to the second type features in the same reticle using different sizing rules depending on the dimensions of the second type features.

2. (Original) A method according to claim 1, wherein the results of the relative isolation determining step cause the more isolated first type apertures to be made larger.

3. (Currently amended) A method according to claim 1 ~~or 2~~, wherein the relative isolation is determined against a first threshold, with the more isolated first type apertures being sized a first way and the less isolated first type apertures sized a second way.

Appln No. N/A

Amdt date February 8, 2005

4. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, further comprising the step of extending the size of at least some of the second type apertures in a second dimension orthogonal to a first dimension.

5. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the results of the first dimension determining step cause the second dimension of the smaller second type apertures to be made larger.

6. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the first type features comprises a plurality of holes.

7. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the second type features comprises a plurality of slits.

8. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the results of the first dimension determining step cause the second type apertures to be sized in the second dimension, orthogonal to the first dimension.

9. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the second type apertures corresponding to the second type features with the smaller first dimension are increased in the second dimension more than those with the larger first dimension.

10. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the first dimension is

Appln No. N/A

Amdt date February 8, 2005

compared with a second threshold, with the larger second type apertures being sized a third way and the smaller second type apertures sized a fourth way.

11. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the first dimension of a feature is the length of the feature.

12. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the features are features of memory cells.

13. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the reticle is a Half-Tone Phase Shift Mask.

14. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1 for producing features for a local interconnect layer.

15. (Original) A reticle for exposing a substrate during production of a circuit, comprising:

a plurality of first type apertures sized using different sizing rules depending on the relative isolation of first type features of the circuit corresponding to the first type apertures; and

a plurality of second type apertures sized using different sizing rules depending on the dimensions of second type features of the circuit corresponding to the second type apertures.

16. (Original) A reticle according to claim 15, wherein the more isolated first type apertures are relatively larger than

Appln No. N/A

Amdt date February 8, 2005

the less isolated first type apertures corresponding to the size of features to be produced.

17. (Currently amended) A reticle according to claim ~~15 or 16~~, wherein the first type apertures are apertures for producing holes.

18. (Currently amended) A reticle according to ~~any one of claims 15 to 17~~ claim 15, wherein the second type apertures are apertures for producing slits.

19. (Currently amended) A reticle according to ~~any one of claims 15 to 18~~ claim 15, wherein the size in a first dimension determines size in a second dimension, orthogonal to the first dimension.

20. (Currently amended) A reticle according to ~~any one of claims 15 to 19~~ claim 15, wherein the second type features determined to be small in the first dimension are larger in the second dimension than those determined to be the larger in the first dimension.

21. (Currently amended) A reticle according to ~~any one of claims 15 to 20~~ claim 15, wherein larger and smaller in the first dimension is determined by comparison with a threshold.

22. (Currently amended) A reticle according to ~~any one of claims 15 to 21~~ claim 15, wherein the first dimension of a feature is the length of the feature.

Appln No. N/A
Amdt date February 8, 2005

23. (Currently amended) A reticle according to ~~any one of claims 15 to 22~~ claim 15, wherein the features are features of memory cells.

24. (Currently amended) A reticle according to ~~any one of claims 15 to 23~~ claim 15, wherein the reticle is a Half-Tone Phase Shift Mask.

25. (Currently amended) A reticle according to ~~any one of claims 15 to 24~~ claim 15, being a local interconnect layer reticle.

26. (Currently amended) A reticle designed according to the method of ~~any one of claims 1 to 14~~ claim 1.

27. (Currently amended) ~~A reticle according to any one of claims 15 to 25,~~ A reticle for exposing a substrate during production of a circuit, comprising:

a plurality of first type apertures sized using different sizing rules depending on the relative isolation of first type features of the circuit corresponding to the first type apertures; and

a plurality of second type apertures sized using different sizing rules depending on the dimensions of second type features of the circuit corresponding to the second type apertures, designed according to the method of ~~any one of claims 1 to 14~~ claim 1.

28. (Currently amended) A method of producing an integrated circuit comprising the steps of:

Appln No. N/A

Amdt date February 8, 2005

designing a reticle in accordance with the method of ~~any one of claims 1 to 14~~ claim 14;

producing the so designed reticle; and

using said reticle to expose features of both the first and second types in a single step in at least one layer of at least a portion of the integrated circuit.

29. (Currently amended) A method of producing an integrated circuit comprising using a reticle as defined in ~~any one of claims 15 to 27~~ claim 15 to print features of both the first and second types in a single step in at least a portion of the integrated circuit.

30. (Currently amended) An integrated circuit, at least a portion of which is produced using a reticle as defined in ~~any one of claims 15 to 27~~ claim 15.